IPIC (Intelligent Power IC) High Side Solenoid Driver

HITACHI

ADE-207-207 (Z) 1st Edition July 1996

Description

The HA13705C is high side power driver IC with protectors and diagnostic function. The device is especially designed to switch inductive loads.

Functions

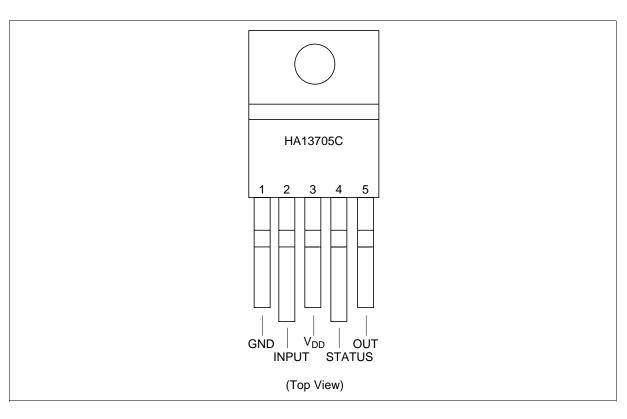
- Power MOS source follower output (2 A)
- With Over Voltage Shut Down circuit (OVSD)
- With Over Current protector circuit (OCSD)
- With Over Temperature Shut Down circuit (OTSD)
- With diagnostic circuit and status output
- With fail safe function under input open circuit condition
- With low voltage inhibit circuit (LVI)
- With output negative voltage clamp circuit

Features

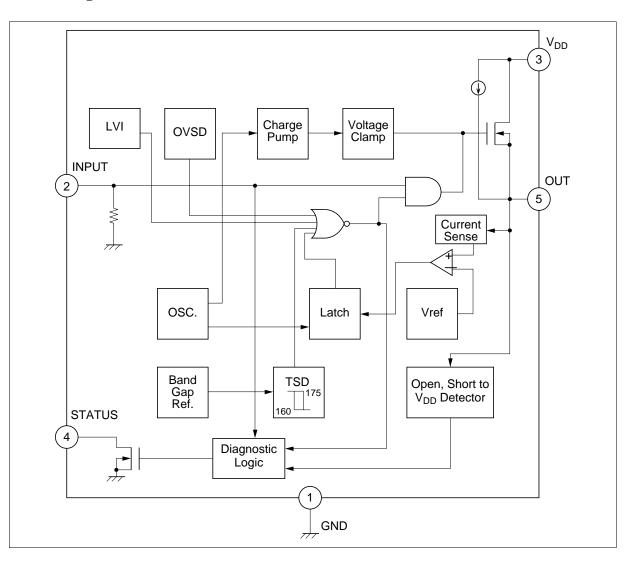
- Protected against 60 V load dump condition
- Low R_{ON} (0.17 Ω Typ)
- www.DataSheetAll.com Wide operating supply voltage range ($V_{DD} = 7 \text{ V to } 25 \text{ V}$)
- High sustaining voltage (-25 V)
- Protected against reverse supply voltage (-13 V)
- Protected against short circuit condition
- Input compatible with TTL, LS-TTL, or 5 V CMOS



Pin Arrangement



Block Diagram



Truth Table

Mode	In	Out	Status	
Normal	L	L	L	
	Н	Н	Н	
Load short	L	L	L	
	Н	L	L	
Load open	L	Н	Н	
	Н	Н	Н	
Short to V _{DD}	L	Н	Н	
	Н	Н	Н	
OTSD *1	L	L	L	
	Н	L	L	
OVSD *2	L	L	Н	
	Н	L	Н	
LVI *3	L	L	Н	
	Н	L	Н	

L: Low level (0.8 V)
H: High level (2.0 V)

Notes: 1. OTSD: Over temperature shut down

2. OVSD: Over voltage shut down

3. LVI: Low voltage inhhibit

Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

Item	Symbol	Rating	Unit	Notes	
Continuous supply voltage	V_{DD}	-13 to 35	V	1	
Transient supply voltage	V _{DD}	60	V	2	
Input voltage	V_{IN}	-0.3 to 30	V		
Output voltage	Vout	–25 to V _{DD}	V	3	
Status voltage	Vs	-0.3 to +15	V		
Output current	lout	_	Α	3, 4	
Status current	ls	5	mA		
Power dissipation	P _T	_	W	5	
Package thermal resistance/ Junction to case	θј−с	5	°C/W		
Package thermal resistance/ Junction to air	θј–а	70	°C/W		
Junction temperature range	Tj	-40 to 150	°C		
Storage temperature range	Tstg	-55 to +150	°C		

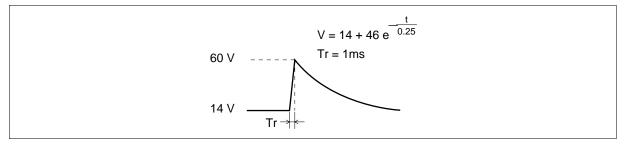
Notes: 1. Recommended operating voltage:

 $V_{DD} = 7 \text{ to } 16 \text{ V (Normal)}$

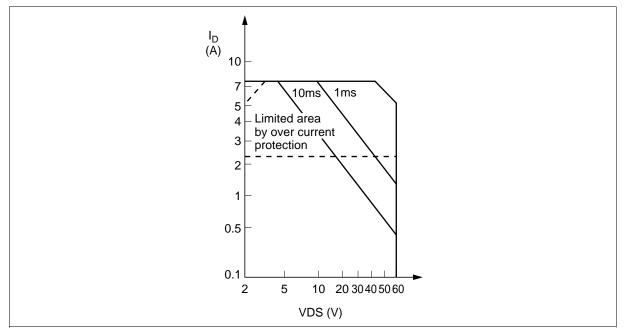
16 to 25 V (Jump up start 5 minutes MAX)

-13 V (Reverse Battely 5 minutes MAX)

2. Load dump condition



3. Output Transistor ASO (Reference Data)



- 4. Internally limited
- 5. Maximum power dissipation $(P_T (Max))$ can be defined as:

 P_T (Max) = (Tjopr(Max) – Tambient) / (θ j-c + θ c-a)

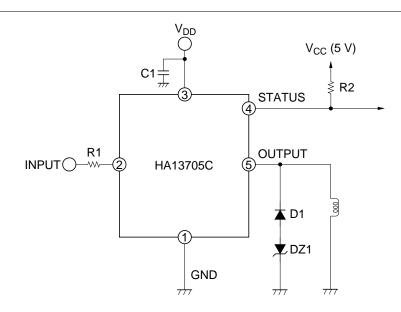
 θ c-a: Thermal resistance between case and air (Depend on heat sink size)

Electrical Characteristics (Ta = 25°C, V_{CC} = 12 V ±10%)

Output R (ON) Ros(ON) Ros(ON) - 0.17 0.36 Ω I ₀ = 2 A (@Tj = -40 to 150°C) 5 Operating supply voltage range V _{DD} 7 - 25 V 3 Quiescent current I _{DD1} - - 0.3 mA V _{IN} = 0 V, Vout = 0 V 3 Output leakage current I _{LEAK} - - 0.1 mA V _{IN} = 5.5 V, Vout = 0 PC 3 Input threshold voltage V _{IL} - - 0.8 V - 2 Input current I _{IL} -10 - 60 μA V _{IN} = 0.8 V 2 Input current I _{IL} -10 - 60 μA V _{IN} = 0.8 V 2 Input current I _{IL} -10 - 60 μA V _{IN} = 0.8 V 2 Input current I _{IL} -10 - 50 μs I _I - 2,5 - - - <	Item		Symbol	Min	Тур	Max	Unit	Test Conditions	Pin	Note
Voltage range Quiescent current I _{DD1} — — — — — — — — — — — — — — — — — — —	Output R (ON)		R _{DS(ON)}	_	0.17	0.36	Ω		5	
Output leakage current I _{LEAK}			V_{DD}	7	_	25	V		3	
Output leakage current I_LEAK — — 0.1 mA V _{DO} = 25 V, V _N = 0 V, V 5 Input threshold voltage V _{IL} — — 0.8 V 2 V _{IN} 2.0 — — V — 2 Input current I _{IL} —10 — 60 µA V _{IN} = 0.8 V 2 Input current I _{IL} —10 — 60 µA V _{IN} = 5.0 V 2 Propagation delay time to del	Quiescer	nt current	I _{DD1}	_	_	0.3	mA	$V_{IN} = 0 \text{ V}, \text{ Vout} = 0 \text{ V}$	3	
Input threshold voltage			I _{DD2}	_	6.0	10.0	mA	$V_{IN} = 5.5 \text{ V}, \text{ Vout} = \text{open}$	3	
Propagation delay time I I I I I I I I I	Output leakage current		I _{LEAK}	_	_	0.1	mA		5	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Input threshold voltage		V _{IL}	_	_	0.8	V		2	
The color of th			V _{IH}	2.0	_	_	V		2	
Propagation delay time t _{d(ON)}	Input current		I _{IL}	-10	_	60	μΑ	V _{IN} = 0.8 V	2	
Total Color			I _{IH}	50	_	300	μΑ	V _{IN} = 5.0 V	2	
Total Current Total Curre	Propagation delay time		t _{d(ON)}	_	_	50	μs	I _O = 1 A	2, 5	
The following large The following large			t _r	_	_	90	μs	_	5	
Open det. threshold current I _{OD} 2 10 100 μs 4, 5 Current limiter operating level I _{CS} 3.0 4.3 7.5 A 5 LVI operating level L.V.I — 5 6 V 3 Over voltage shut down Operating level OVSD 26 29 33 V 3 Output sustain voltage V _(SUS) — — — — — 25 V lout = 20 mA 5 Over Operating level OTSD 150 175 — °C 5 1 Hysteresis THYS — 15 — °C 5 1 Status on voltage V _{SL} — — 0.4 V I _S = 1 mA 4			t _{d(OFF)}	_	_	50	μs	_	2, 5	
Current limiter operating I cs 3.0 4.3 7.5 A 5 LVI operating level L.V.I — 5 6 V 3 Over voltage voltage level Operating level OVSD 26 29 33 V 3 Hysteresis VHYS 0.15 0.5 1.5 V 3 Output sustain voltage V _(sus) — — —25 V lout = 20 mA 5 Over temperature shut down Operating level OTSD 150 175 — °C 5 1 Hysteresis THYS — 15 — °C 5 1 Status on voltage V _{SL} — — 0.4 V I _S = 1 mA 4			Tf	_	_	50	μs	_	5	
LVI operating level L.V.I — 5 6 V 3			I _{OD}	2	10	100	μs		4, 5	
Over voltage shut down Operating level OVSD 26 29 33 V 3 Hysteresis VHYS 0.15 0.5 1.5 V 3 Output sustain voltage V _(SUS) — — -25 V lout = 20 mA 5 Over temperature shut down Operating level OTSD 150 175 — °C 5 1 Hysteresis THYS — 15 — °C 5 1 Status on voltage V _{SL} — — 0.4 V I _S = 1 mA 4	-		I _{CS}	3.0	4.3	7.5	Α		5	
voltage shut down level Hysteresis VHYS 0.15 0.5 1.5 V 3 Output sustain voltage V _(SUS) — — — —25 V lout = 20 mA 5 Over temperature shut down Hysteresis THYS — 15 — °C 5 1 Status on voltage V _{SL} — — 0.4 V I _S = 1 mA 4	LVI opera	ating level	L.V.I	_	5	6	V		3	
Output sustain voltage $V_{(SUS)}$ — — — — — — — $^{\circ}C$	voltage shut		OVSD	26	29	33	V		3	
Over temperature shut down Operating level OTSD 150 175 — °C 5 1 Hysteresis THYS — 15 — °C 5 1 Status on voltage V _{SL} — — 0.4 V I _S = 1 mA 4		Hysteresis	VHYS	0.15	0.5	1.5	V		3	
	Output sustain voltage		$V_{(SUS)}$	_	_	-25	V	lout = 20 mA	5	
Status on voltage V_{SL} — 0.4 V $I_S = 1 \text{ mA}$ 4	temper- ature shut			150	175	_	°C		5	1
		Hysteresis	THYS	_	15	_	°C		5	1
Status leakage current $I_{S(Leak)}$ -10 — 100 μA $V_s = 5.0 \text{ V}$ 4	Status on voltage		V _{SL}	_	_	0.4	V	I _S = 1 mA	4	
	Status leakage current		S(Leak)	-10	_	100	μΑ	V _S = 5.0 V	4	

Notes: 1. Design parameter only (no test)

Solenoid Drive Application and it's Waveform

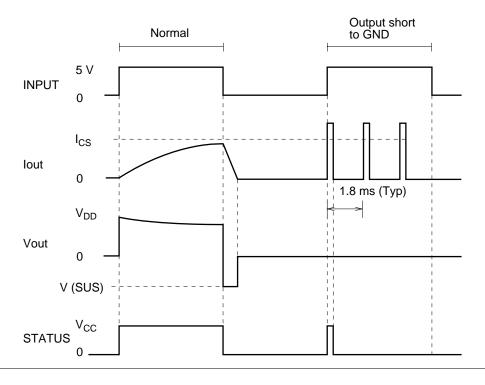


R1: Input series resistance to protect CMOS driver.

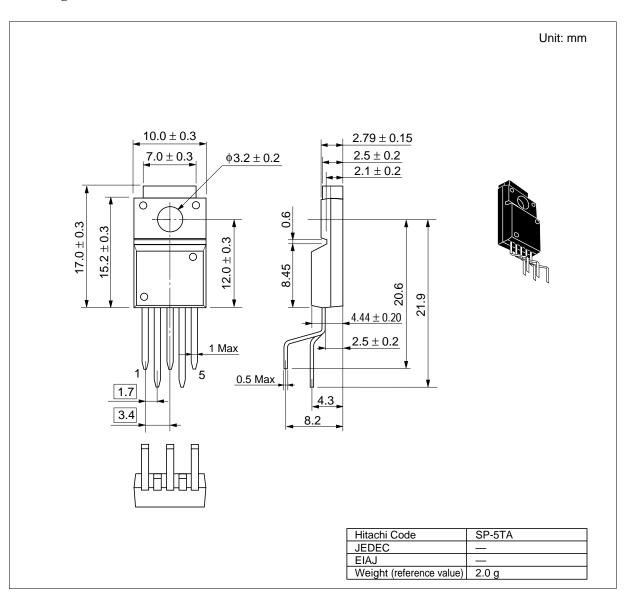
R2 : Pull up resistance at status output.

C1: The capacitor to compensate the inductance at $V_{\mbox{\scriptsize DD}}$ line.

D1, DZ1: for Reverse voltage clamp



Package Dimensions



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